Electronic Supplementary Material (ESI) for Physical Chemistry Chemical Physics.

Novel Germanene-Arsenene and Germanene-Antimonene Lateral Heterostructures: Interline-dependent Electronic and Magnetic Properties

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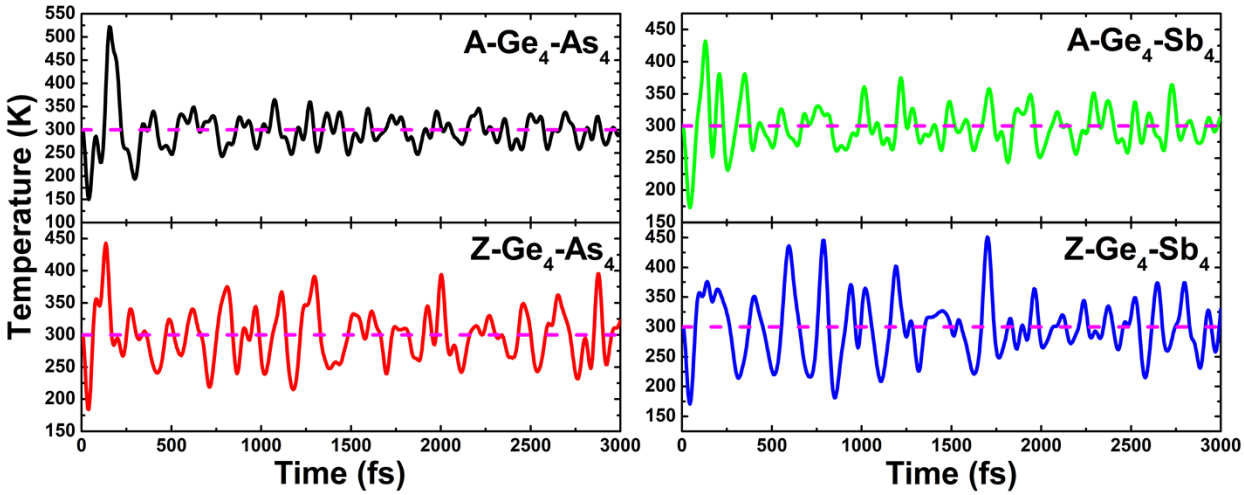

Figure S1: AIMD simulations at 300 K of germanene-arsenene and germanene-antimonene lateral heterostructures.

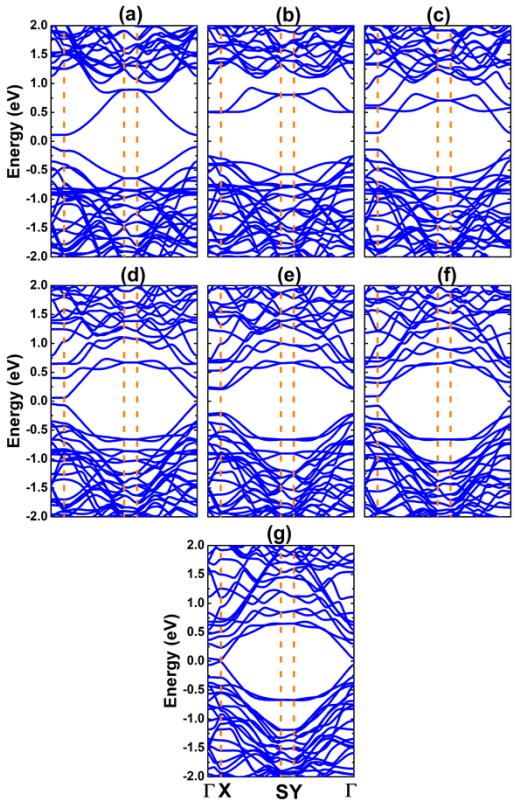

Figure S2: Electronic band structure (Blue curve: non-spin polarization) of armchair-interline Ge_m-Sb_{8-m} lateral heterostructures with (a) m = 1, (b) m = 2, (c) m = 3, (d) m = 4, (e) m = 5, (f) m = 6, and (g) m = 7.

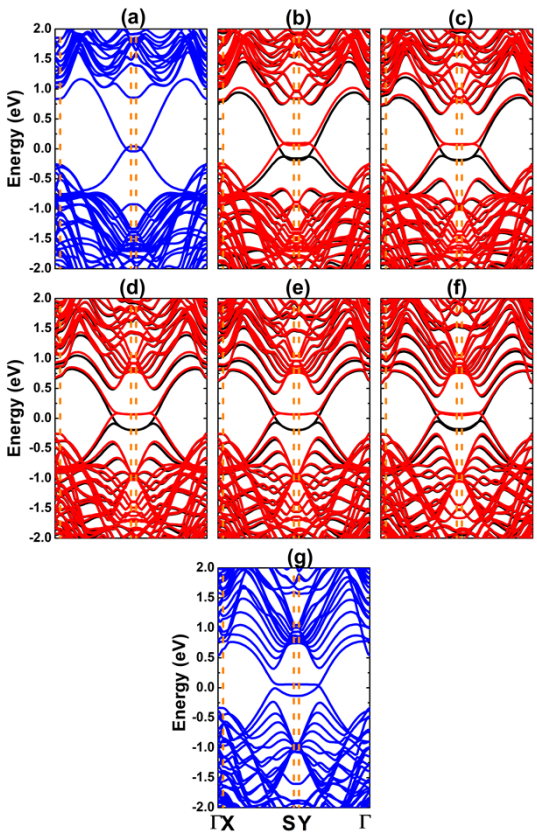

Figure S3: Electronic band structure (Blue curve: non-spin polarization; Black curve: spin-up; Red curve: spin-down) of zigzag-interline Ge_m-Sb_{8-m} lateral heterostructures with (a) m = 1, (b) m = 2, (c) m = 3, (d) m = 4, (e) m = 5, (f) m = 6, and (g) m = 7.